imall

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Panasonic

FC4B22270L1

MOS FET FC4B22270L1

Gate resistor installed Dual N-channel MOS FET

For lithium-ion secondary battery protection circuits

Features

- Low source-source ON resistance:Rss(on) typ. = 18 mΩ(VGS = 3.8 V)
- CSP(Chip Size Package)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL : Level 1)
- Marking Symbol: 2J

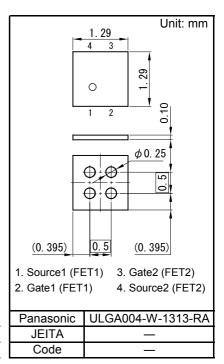
Packaging

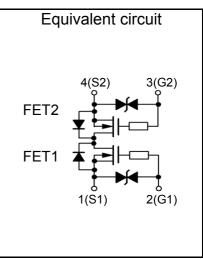
Embossed type (Thermo-compression sealing): 1 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C							
Parameter	Symbol	Rating	Unit				
Source-source Voltage	VSS	20	V				
Gate-source Voltage	VGS	±12	V				
Source Current (DC)	IS *1	4	A				
	IS *2	8					
Source Current (Pulsed)	ISp *2	40	А				
Total Power Dissipation	PD ^{*1}	0.37	W				
	PD ^{*2}	1.5					
Channel Temperature	Tch	150	°C				
Storage Temperature Range	Tstg	-55 to +150	°C				
Thermal Resistance (ch-a)	Rth ^{*1}	338	°C/W				
	Rth ^{*2}	83					

Note *1 Mounted on FR4 board (25.4 mm \times 25.4 mm \times t1.0 mm) using the minimum recommended pad size (36µm Copper).

- *2 Mounted on Ceramic substrate (70 mm \times 70 mm \times t1.0 mm).
- *3 t = 10 μ s, Duty Cycle \leq 1 %





Panasonic

MOS FET FC4B22270L1

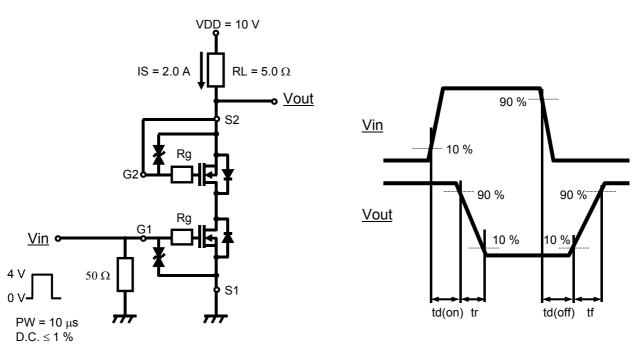
■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Source-source Breakdown Voltage	VSSS	IS = 1 mA, VGS = 0 V	20			V
Zero Gate Voltage Source Current	ISSS	VSS = 20 V, VGS = 0 V			1.0	μA
Gate-source Leakage Current	IGSS	VGS = ±8 V, VSS = 0 V			±10	μA
Gate-source Threshold Voltage	Vth	IS = 0.31 mA, VSS = 10 V	0.35	0.90	1.4	V
Source-source On-state Resistance	RSS(on)1	· · ·	12	17	22	mΩ
	RSS(on)2	IS = 2.0 A, VGS = 3.8 V	12.5	18	23	
	RSS(on)3	IS = 2.0 A, VGS = 3.1 V	13.5	19	26.5	
	RSS(on)4	IS = 2.0 A, VGS = 2.5 V	14	22	37	
Body Diode Forward Voltage	VF(s-s)	IF = 2.0 A, VGS = 0 V		0.8	1.2	V
Input Capacitance ^{*1}	Ciss			910		pF
Output Capacitance ^{*1}	Coss	VSS = 10 V, VGS = 0 V, f = 1 KHz		105		
Reverse Transfer Capacitance *1	Crss			80		
Turn-on delay Time *1,*2	td(on)	VDD = 10 V, VGS = 0 to 4.0 V		0.25		μS
Rise Time ^{*1,*2}	tr	IS = 2.0 A		0.55		
Turn-off delay Time *1,*2	td(off)	VDD = 10 V, VGS = 4.0 to 0 V 1.65 IS = 2.0 A 1.0				
Fall Time ^{*1,*2}	tf			1.0		μS
Total Gate Charge ^{*1}	Qg	VDD = 10 V		9		
Gate-source Charge ^{*1}	Qgs	VGS = 0 to 4.0 V, IS = 2.0 A		2.6		nC
Gate-drain Charge ^{*1}	Qgd			2.4		

Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

*1 Guaranteed by design, not subject to production testing

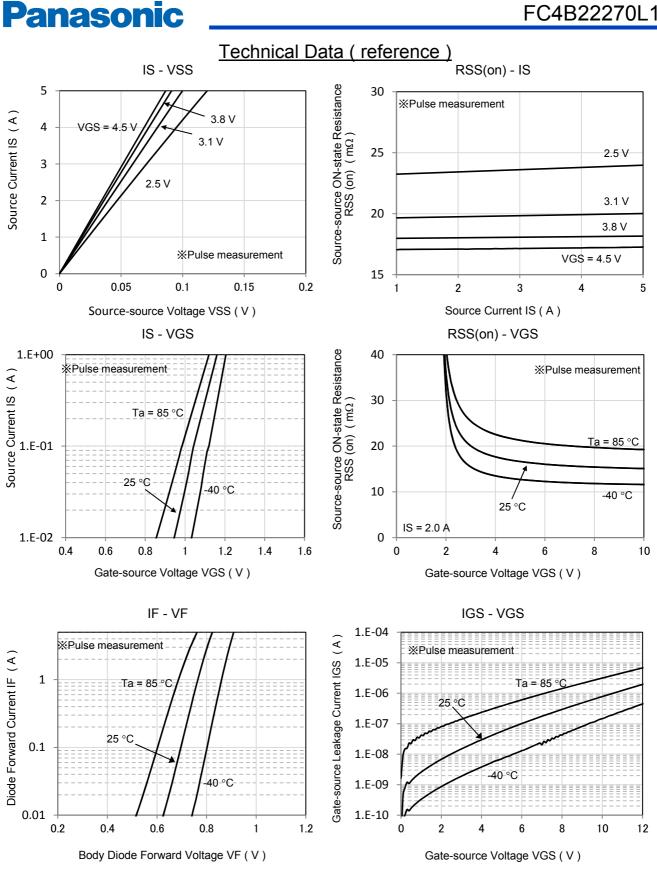
*2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time



Note2:Measurement circuit

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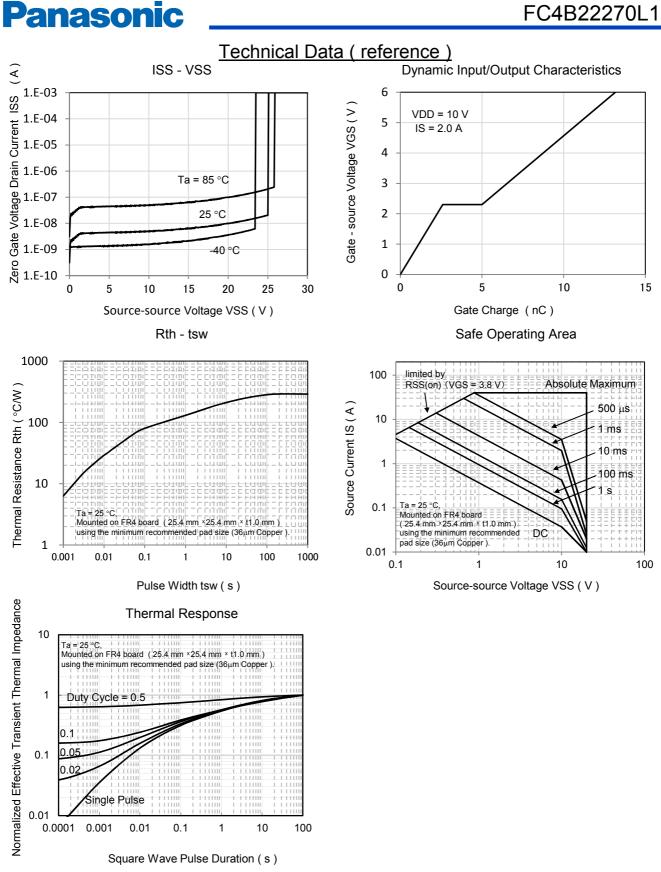
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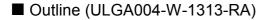
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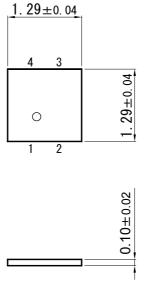
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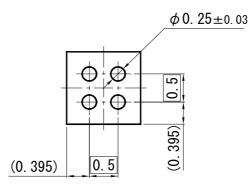


MOS FET FC4B22270L1

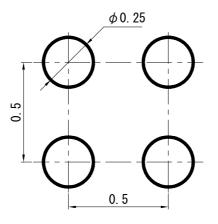
Unit: mm







Land Pattern (Reference)



Unit: mm

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